

# THYRISTOR(Through Hole/Non-isolated)

# SMG3D60C

(Sensitive Gate)

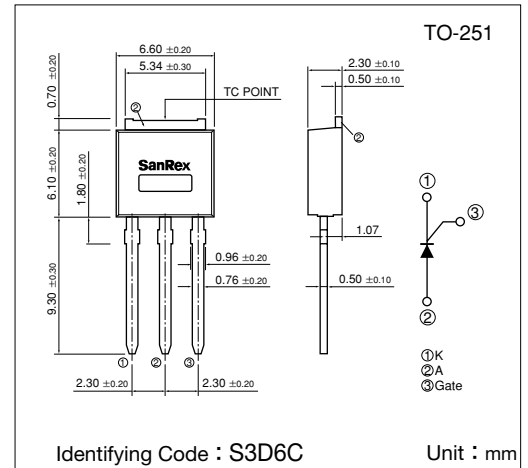
**SanRex** Thyristor **SMG3D60C** is designed for full wave AC control applications. It can be used as an ON/OFF function or for phase control operation.

### Typical Applications

- Home Appliances : Electric Blankets, Starter for FL, other control applications
- Industrial Use : SMPS, Solenoid for Breakers, Motor Controls, Heater Controls, other control applications

### Features

- $I_{T(AV)}=3A$
- High Surge Current
- Low Voltage Drop
- Lead-Free Package



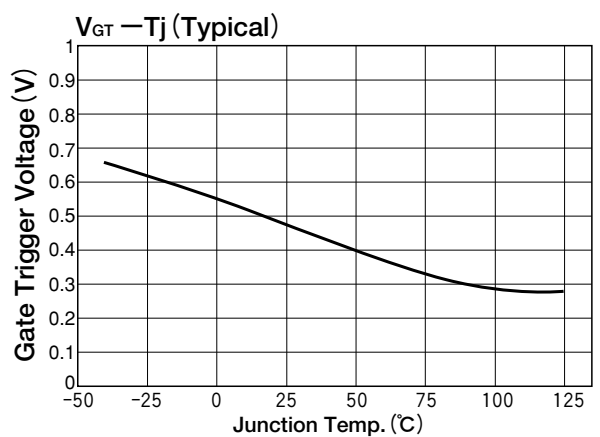
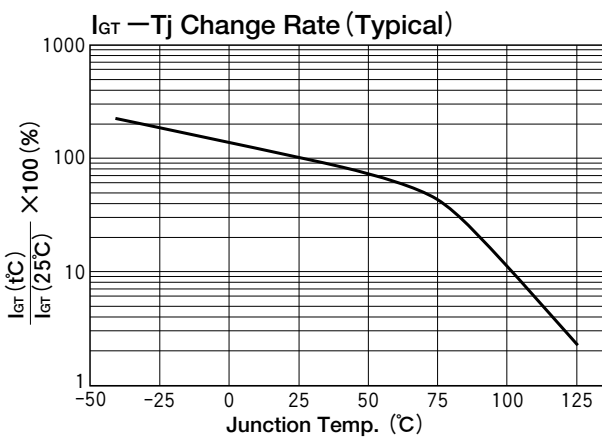
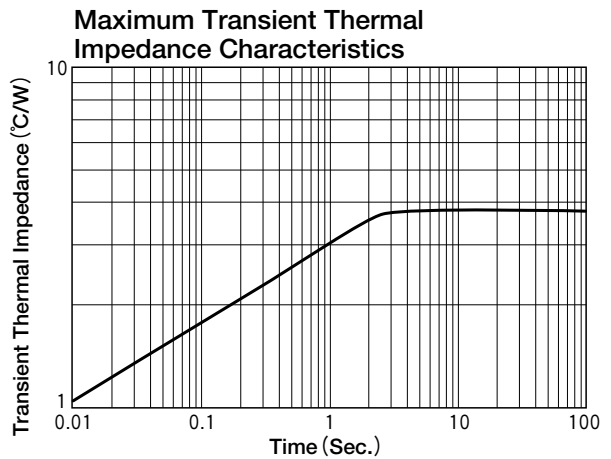
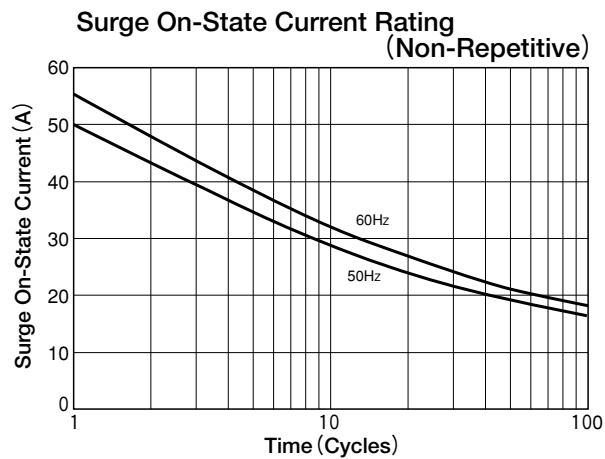
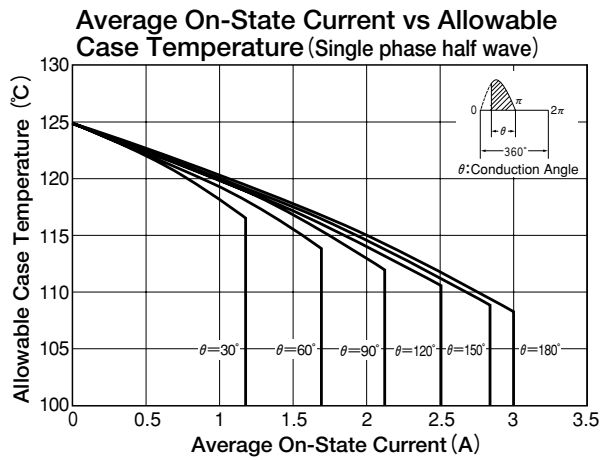
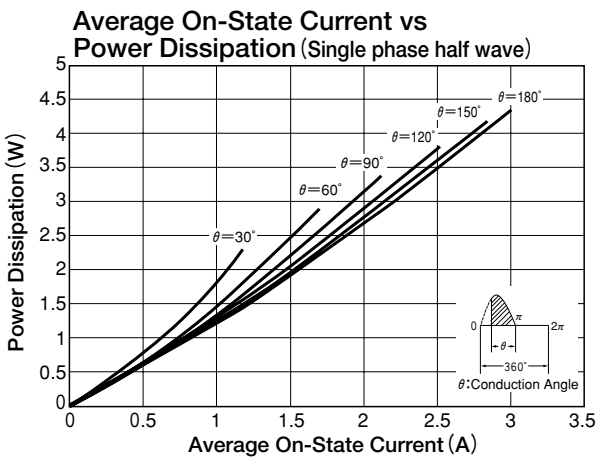
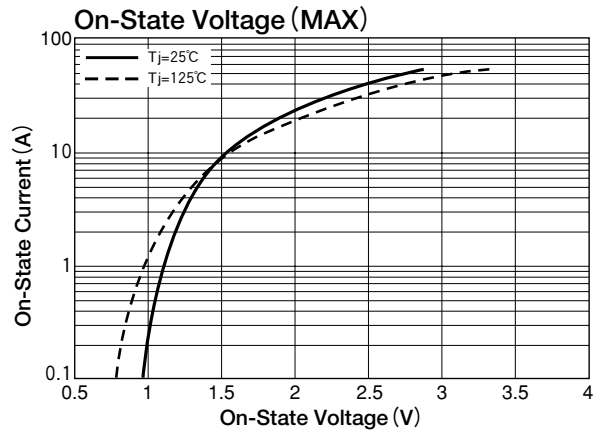
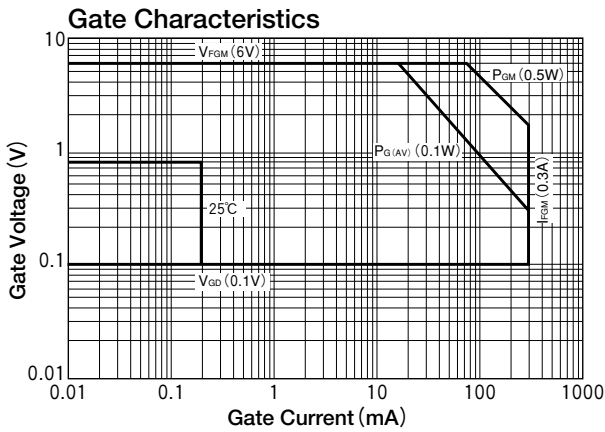
### Maximum Ratings

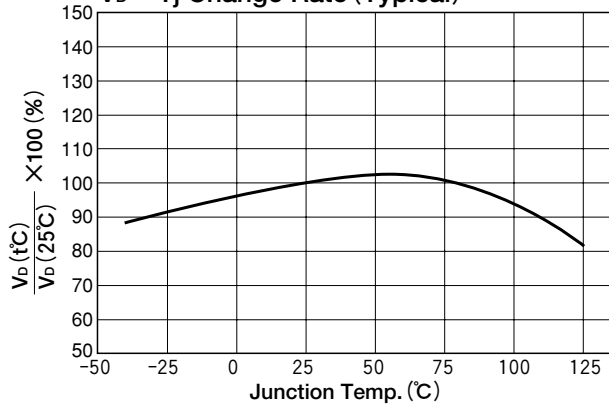
( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Item	Reference	Ratings	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		600	V
$V_{RSM}$	Non-Repetitive Peak Reverse Voltage		720	V
$V_{DRM}$	Repetitive Peak Off-State Voltage		600	V
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, $180^\circ$ conduction, $T_c=108^\circ\text{C}$	3	A
$I_{T(RMS)}$	R.M.S. On-State Current	Single phase, half wave, $180^\circ$ conduction, $T_c=108^\circ\text{C}$	4.7	A
$I_{TSM}$	Surge On-State Current	50Hz/60Hz, $\frac{1}{2}$ cycle Peak value, non-repetitive	50/55	A
$I^2t$	$I^2t$		12.5	$A^2S$
$P_{GM}$	Peak Gate Power Dissipation		0.5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.1	W
$I_{FGM}$	Peak Gate Current		0.3	A
$V_{FGM}$	Peak Gate Voltage (Forward)		6	V
$V_{RGM}$	Peak Gate Voltage (Reverse)		6	V
$T_j$	Operating Junction Temperature		$-40 \sim +125$	$^\circ\text{C}$
$T_{stg}$	Storage Temperature		$-40 \sim +150$	$^\circ\text{C}$
	Mass		0.39	g

### Electrical Characteristics

Symbol	Item	Reference	Ratings			Unit
			Min.	Typ.	Max.	
$I_{DRM}$	Repetitive Peak Off-State Current	$T_j=125^\circ\text{C}$ , $V_D=V_{DRM}$ , $R_{GK}=220\ \Omega$			1	mA
$I_{RRM}$	Repetitive Peak Reverse Current	$T_j=125^\circ\text{C}$ , $V_R=V_{RRM}$ , $R_{GK}=220\ \Omega$			1	mA
$V_{TM}$	Peak On-State Voltage	$I_T=9A$ , Inst. measurement			1.5	V
$I_{GT}$	Gate Trigger Current	$V_D=6V$ , $R_L=10\ \Omega$	1		200	$\mu A$
$V_{GT}$	Gate Trigger Voltage				0.8	V
$V_{GD}$	Non-Trigger Gate Voltage	$T_j=125^\circ\text{C}$ , $V_D=\frac{1}{2}V_{DRM}$ , $R_{GK}=220\ \Omega$	0.1			V
$I_H$	Holding Current	$R_{GK}=220\ \Omega$		3.5		mA
$R_{th(j-c)}$	Thermal Resistance	Junction to case			3.8	$^\circ\text{C/W}$



**$V_D - T_j$  Change Rate (Typical)** **$V_R - T_j$  Change Rate (Typical)**